Takaaki Mano

List of Publications by Year
in descending order

226 papers	4,210 citations	117625 34 h-index	149698 56 g-index
227 all docs	227 docs citations	227 times ranked	2253 citing authors

#	Article	IF	Citations
1	Self-Assembly of Concentric Quantum Double Rings. Nano Letters, 2005, 5, 425-428.	9.1	357
2	Optical transitions in quantum ring complexes. Physical Review B, 2005, 72, .	3.2	204
3	Nanometer-scale GaAs ring structure grown by droplet epitaxy. Journal of Crystal Growth, 2005, 278, 108-112.	1.5	151
4	Formation and Microstructures of Anodic Alumina Films from Aluminum Sputtered on Glass Substrate. Journal of the Electrochemical Society, 2002, 149, B321.	2.9	144
5	Symmetric quantum dots as efficient sources of highly entangled photons: Violation of Bell's inequality without spectral and temporal filtering. Physical Review B, 2013, 88, .	3.2	116
6	Self-assembly of laterally aligned GaAs quantum dot pairs. Applied Physics Letters, 2006, 89, 113115.	3.3	110
7	Formation of InAs quantum dot arrays on GaAs (100) by self-organized anisotropic strain engineering of a (In,Ga)As superlattice template. Applied Physics Letters, 2002, 81, 1705-1707.	3.3	90
8	Exciton fine structure in strain-free<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaAs</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>Al</mml:m dots: Extrinsic effects. Physical Review B, 2008, 78, .	3.2	89
9	Self-Assembly of Symmetric GaAs Quantum Dots on (111)A Substrates: Suppression of Fine-Structure Splitting. Applied Physics Express, 2010, 3, 065203.	2.4	77
10	Temperature dependence of the photoluminescence of InGaAs/GaAs quantum dot structures without wetting layer. Applied Physics Letters, 2002, 81, 3067-3069.	3.3	70
11	Impact of heavy hole-light hole coupling on optical selection rules in GaAs quantum dots. Applied Physics Letters, 2010, 97, .	3.3	70
12	Fabrication of InGaAs quantum dots on GaAs(001) by droplet epitaxy. Journal of Crystal Growth, 2000, 209, 504-508.	1.5	67
13	New Self-Organized Growth Method for InGaAs Quantum Dots on GaAs(001) Using Droplet Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L1009-L1011.	1.5	66
14	Ultra-narrow emission from single GaAs self-assembled quantum dots grown by droplet epitaxy. Nanotechnology, 2009, 20, 395601.	2.6	65
15	Nanoscale InGaAs concave disks fabricated by heterogeneous droplet epitaxy. Applied Physics Letters, 2000, 76, 3543-3545.	3.3	64
16	Spectral diffusion and line broadening in single self-assembled GaAsâˆ'AlGaAs quantum dot photoluminescence. Applied Physics Letters, 2008, 93, .	3.3	62
17	Ring-shaped GaAs quantum dot laser grown by droplet epitaxy: Effects of post-growth annealing on structural and optical properties. Journal of Crystal Growth, 2007, 301-302, 740-743.	1.5	61
18	Atomic scale analysis of self assembled GaAs/AlGaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2010, 96, .	3.3	60

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19	Direct imaging of self-organized anisotropic strain engineering for improved one-dimensional ordering of (In,Ga)As quantum dot arrays. Journal of Applied Physics, 2004, 95, 109-114.	2.5	54
20	Lasing in GaAsâˆ•AlGaAs self-assembled quantum dots. Applied Physics Letters, 2006, 89, 183102.	3.3	50
21	Scroll-like Alloyed CdS_{<i>x</i>}Se_{1â€–<i>x</i>} Nanoplatelets: Facile Synthesis and Detailed Analysis of Tunable Optical Properties. Chemistry of Materials, 2017, 29, 579-586.	6.7	49
22	Photon antibunching in double quantum ring structures. Physical Review B, 2009, 79, .	3.2	44
23	Self-Limiting Growth of Hexagonal and Triangular Quantum Dots on (111)A. Crystal Growth and Design, 2012, 12, 1411-1415.	3.0	44
24	Poissonian statistics of excitonic complexes in quantum dots. Journal of Applied Physics, 2009, 106, .	2.5	42
25	Role of the continuum background for carrier relaxation in InAs quantum dots. Physical Review B, 2005, 72, .	3.2	41
26	Dark-Bright Mixing of Interband Transitions in Symmetric Semiconductor Quantum Dots. Physical Review Letters, 2011, 107, 166604.	7.8	41
27	Vanishing fine-structure splittings in telecommunication-wavelength quantum dots grown on (111)A surfaces by droplet epitaxy. Physical Review B, 2014, 90, .	3.2	41
28	Rapid thermal annealing effects on self-assembled quantum dot and quantum ring structures. Journal of Applied Physics, 2008, 104, .	2.5	40
29	Synchronously wired infrared antennas for resonant single-quantum-well photodetection up to room temperature. Nature Communications, 2020, 11, 565.	12.8	40
30	InAs nanocrystal growth on Si (100). Applied Surface Science, 1998, 130-132, 760-764.	6.1	39
31	Optically monitored nuclear spin dynamics in individual GaAs quantum dots grown by droplet epitaxy. Physical Review B, 2008, 78, .	3.2	38
32	Optical properties of GaSb/GaAs type-Ð†Ð† quantum dots grown by droplet epitaxy. Applied Physics Letters, 2009, 94, 081911.	3.3	37
33	Nuclear magnetization in gallium arsenide quantum dots at zero magnetic field. Nature Communications, 2014, 5, 3268.	12.8	37
34	GaAsâˆ•AlGaAs quantum dot laser fabricated on GaAs (311)A substrate by droplet epitaxy. Applied Physics Letters, 2008, 93, 203110.	3.3	35
35	Energy renormalization of exciton complexes in GaAs quantum dots. Physical Review B, 2010, 82, .	3.2	34
36	Precise shape engineering of epitaxial quantum dots by growth kinetics. Physical Review B, 2015, 92, .	3.2	34

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37	Extremely high-density GaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2012, 100, .	3.3	33
38	Size-dependent line broadening in the emission spectra of single GaAs quantum dots: Impact of surface charge on spectral diffusion. Physical Review B, 2015, 92, .	3.2	33
39	Carrier dynamics in individual concentric quantum rings: Photoluminescence measurements. Physical Review B, 2008, 77, .	3.2	32
40	Complex quantum dot arrays formed by combination of self-organized anisotropic strain engineering and step engineering on shallow patterned substrates. Journal of Applied Physics, 2005, 97, 014304.	2.5	28
41	Unstrained GaAs Quantum Dashes Grown on GaAs(001) Substrates by Droplet Epitaxy. Applied Physics Express, 2010, 3, 045502.	2.4	28
42	Effect of annealing on formation of self-assembled (In,Ga)As quantum wires on GaAs (100) by molecular beam epitaxy. Journal of Applied Physics, 2002, 92, 4043-4046.	2.5	27
43	Strain relaxation in InAs heteroepitaxy on lattice-mismatched substrates. Scientific Reports, 2020, 10, 4606.	3.3	27
44	Bunching visibility for correlated photons from single GaAs quantum dots. Physical Review B, 2009, 79, .	3.2	25
45	High-density GaAs/AlGaAs quantum dots formed on GaAs (311)A substrates by droplet epitaxy. Journal of Crystal Growth, 2009, 311, 1828-1831.	1.5	24
46	Magnetic field induced valence band mixing in [111] grown semiconductor quantum dots. Physical Review B, 2013, 87, .	3.2	24
47	Droplet epitaxial growth of highly symmetric quantum dots emitting at telecommunication wavelengths on InP(111)A. Applied Physics Letters, 2014, 104, .	3.3	24
48	InAs Quantum Dots Growth by Modified Droplet Epitaxy Using Sulfur Termination. Japanese Journal of Applied Physics, 2000, 39, 4580-4583.	1.5	23
49	Final-state readout of exciton qubits by observing resonantly excited photoluminescence in quantum dots. Applied Physics Letters, 2007, 90, 051909.	3.3	23
50	Photon Correlation in GaAs Self-Assembled Quantum Dots. Applied Physics Express, 0, 1, 042001.	2.4	23
51	Self-assembly of quantum dots and rings by droplet epitaxy and their optical properties. Journal of Nanophotonics, 2009, 3, 031605.	1.0	23
52	Magneto-optical properties of excitonic complexes in GaAs self-assembled quantum dots. Physical Review B, 2010, 81, .	3.2	23
53	Geometrical impact on the optical polarization of droplet epitaxial quantum dots. Physical Review B, 2012, 86, .	3.2	23
54	Voltage dependence of two-step photocurrent generation in quantum dot intermediate band solar cells. Solar Energy Materials and Solar Cells, 2015, 134, 108-113.	6.2	23

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55	Characterization of strain distribution in quantum dots by X-ray diffraction. Journal of Crystal Growth, 2002, 234, 197-201.	1.5	21
56	Single photon emission from droplet epitaxial quantum dots in the standard telecom window around a wavelength of 1.55Âµm. Applied Physics Express, 2020, 13, 025002.	2.4	20
57	Cross-sectional scanning tunneling microscopy study of InGaAs quantum dots on GaAs(001) grown by heterogeneous droplet epitaxy. Applied Physics Letters, 2002, 80, 4345-4347.	3.3	19
58	Self-organized anisotropic strain engineering: a new concept for quantum dot ordering. Proceedings of the IEEE, 2003, 9, 1898-1906.	21.3	19
59	Temperature-Dependent Photoluminescence of Self-Assembled (In,Ga)As Quantum Dots on GaAs (100): Carrier Redistribution through Low-Energy Continuous States. Japanese Journal of Applied Physics, 2005, 44, 6829-6832.	1.5	19
60	Coupled quantum nanostructures formed by droplet epitaxy. Thin Solid Films, 2006, 515, 531-534.	1.8	19
61	Fabrication of a complex InAs ring-and-dot structure by droplet epitaxy. Applied Surface Science, 2008, 254, 7777-7780.	6.1	19
62	Bunched photon statistics of the spectrally diffusive photoluminescence of single self-assembled GaAs quantum dots. Physical Review B, 2012, 86, .	3.2	19
63	Stable and efficient collection of single photons emitted from a semiconductor quantum dot into a single-mode optical fiber. Applied Physics Express, 2016, 9, 032801.	2.4	19
64	Self-assembly of vertically aligned quantum ring-dot structure by Multiple Droplet Epitaxy. Journal of Crystal Growth, 2017, 477, 239-242.	1.5	19
65	Structural properties of GaAs nanostructures formed by a supply of intense As4 flux in droplet epitaxy. Applied Surface Science, 2008, 254, 7770-7773.	6.1	18
66	Acceleration and suppression of photoemission of GaAs quantum dots embedded in photonic crystal microcavities. Applied Physics Letters, 2008, 93, 111103.	3.3	18
67	Extremely High- and Low-Density of Ga Droplets on GaAs{111}A,B: Surface-Polarity Dependence. Crystal Growth and Design, 2015, 15, 485-488.	3.0	18
68	Excitonic transitions in semiconductor concentric quantum double rings. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 46-48.	2.7	17
69	Anisotropic Diffusion of In Atoms from an In Droplet and Formation of Elliptically Shaped InAs Quantum Dot Clusters on (100) GaAs. Crystal Growth and Design, 2011, 11, 726-728.	3.0	17
70	Field control of anisotropic spin transport and spin helix dynamics in a modulation-doped GaAs quantum well. Physical Review B, 2018, 97, .	3.2	17
71	Growth of GaSb dots on GaAs(100) by droplet epitaxy. Physica Status Solidi (B): Basic Research, 2009, 246, 733-735.	1.5	16
72	Effect of off-cut angle of hydrogen-terminated diamond(111) substrate on the quality of AlN towards high-density AlN/diamond(111) interface hole channel. Journal of Applied Physics, 2017, 121, .	2.5	16

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73	Growth of Metamorphic InGaAs on GaAs (111)A: Counteracting Lattice Mismatch by Inserting a Thin InAs Interlayer. Crystal Growth and Design, 2016, 16, 5412-5417.	3.0	15
74	Morphological control of GaAs quantum dots grown by droplet epitaxy using a thin AlGaAs capping layer. Journal of Applied Physics, 2010, 108, 083505.	2.5	14
75	Structural atomic-scale analysis of GaAs/AlGaAs quantum wires and quantum dots grown by droplet epitaxy on a (311)A substrate. Applied Physics Letters, 2011, 98, 193112.	3.3	14
76	Self-assembly of InAs ring complexes on InP substrates by droplet epitaxy. Journal of Applied Physics, 2012, 112, 063510.	2.5	14
77	Two-Step Formation of Gallium Droplets with High Controllability of Size and Density. Crystal Growth and Design, 2011, 11, 4647-4651.	3.0	13
78	Lasing in ultra-narrow emission from GaAs quantum dots coupled with a two-dimensional layer. Nanotechnology, 2011, 22, 335201.	2.6	13
79	Shape control of quantum dots studied by cross-sectional scanning tunneling microscopy. Journal of Applied Physics, 2011, 109, 102413.	2.5	13
80	Composition profiling of GaAs/AlGaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2014, 105, .	3.3	13
81	Direct visualization of the N impurity state in dilute GaNAs using scanning tunneling microscopy. Nanoscale, 2015, 7, 16773-16780.	5.6	13
82	Droplet epitaxy growth of telecom InAs quantum dots on metamorphic InAlAs/GaAs(111)A. Japanese Journal of Applied Physics, 2015, 54, 04DH07.	1.5	13
83	Optically Imaged Striped Domains of Nonequilibrium Electronic and Nuclear Spins in a Fractional Quantum Hall Liquid. Physical Review Letters, 2017, 118, 076802.	7.8	13
84	Near-field resonant photon sorting applied: dual-band metasurface quantum well infrared photodetectors for gas sensing. Nanophotonics, 2020, 9, 4775-4784.	6.0	13
85	Fabrication of GaNAs/AlGaAs Heterostructures with Large Band Offset Using Periodic Growth Interruption. Applied Physics Express, 2011, 4, 125001.	2.4	12
86	Charge tuning in [111] grown GaAs droplet quantum dots. Applied Physics Letters, 2014, 105, 082111.	3.3	12
87	Indium segregation in the fabrication of InGaAs concave disks by heterogeneous droplet epitaxy. Journal of Crystal Growth, 2001, 227-228, 1069-1072.	1.5	11
88	High-resolution core-level photoemission study on GaAs(111)B surfaces. Journal of Applied Physics, 2007, 101, 043516.	2.5	11
89	Two different growth modes of GaSb dots on GaAs(100) by droplet epitaxy. Journal of Crystal Growth, 2009, 311, 2255-2257.	1.5	11
90	Heteroepitaxy of GaSb on Si(111) and fabrication of HfO2/GaSb metal-oxide-semiconductor capacitors. Applied Physics Letters, 2014, 104, .	3.3	11

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91	Hyperfine coupling of hole and nuclear spins in symmetric (111)-grown GaAs quantum dots. Physical Review B, 2016, 94, .	3.2	11
92	Current-injection quantum-entangled-pair emitter using droplet epitaxial quantum dots on GaAs(111)A. Applied Physics Letters, 2019, 115, .	3.3	11
93	Transport of a persistent spin helix drifting transverse to the spin texture. Physical Review B, 2019, 99, .	3.2	11
94	Droplet Epitaxy Quantum Ring Structures. Journal of Nanoelectronics and Optoelectronics, 2011, 6, 34-50.	0.5	11
95	Role of In desorption for formation of self-organized (In,Ga)As quantum wires on GaAs(100) during superlattice formation. Journal of Crystal Growth, 2003, 251, 264-268.	1.5	10
96	Phonon sideband recombination kinetics in single quantum dots. Journal of Applied Physics, 2008, 104, .	2.5	10
97	Fine structure splitting of quantum dot excitons: Role of geometry and environment. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 881-883.	2.7	10
98	Visible single-photon emission from a nitrogen impurity center in AlAs. Applied Physics Letters, 2013, 102, .	3.3	10
99	Self-Assembled Growth of Ga Droplets on GaAs(001): Role of Surface Reconstructions. Crystal Growth and Design, 2014, 14, 3110-3115.	3.0	10
100	Growth and optical properties of GaSb/GaAs type-II quantum dots with and without wetting layer. Japanese Journal of Applied Physics, 2015, 54, 04DH01.	1.5	10
101	Magnetospectroscopy of excited states in charge-tunable GaAs/AlGaAs [111] quantum dots. Physical Review B, 2016, 93, .	3.2	10
102	Wavelength extension beyond 1.5 Âµm in symmetric InAs quantum dots grown on InP(111)A using droplet epitaxy. Applied Physics Express, 2016, 9, 101201.	2.4	10
103	Systematic studies for improving device performance of quantum well infrared stripe photodetectors. Nanophotonics, 2020, 9, 3373-3384.	6.0	10
104	Generalized Grazing Incidence-Angle X-Ray Diffraction Studies on InAs Quantum Dots on Si (100) Substrates. Japanese Journal of Applied Physics, 2000, 39, 4483-4485.	1.5	9
105	Ordering of GaAs quantum dots by droplet epitaxy. Physica Status Solidi (B): Basic Research, 2009, 246, 729-732.	1.5	9
106	Distribution of exciton emission linewidth observed for GaAs quantum dots grown by droplet epitaxy. Journal of Luminescence, 2010, 130, 2390-2393.	3.1	9
107	Mid-IR Dirac-cone dispersion relation materialized in SOI photonic crystal slabs. Optics Express, 2020, 28, 4194.	3.4	9
108	Two-Color Photoexcitation in a GaNAs/AlGaAs Quantum Well Solar Cell. Japanese Journal of Applied Physics, 2012, 51, 06FF15.	1.5	9

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109	Effects of low-temperature capping on the optical properties of GaAs/AlGaAs quantum wells. Nanoscale Research Letters, 2011, 6, 76.	5.7	8
110	Selfâ€assembled GaAs quantum dots coupled with GaAs wetting layer grown on GaAs (311)A by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 257-259.	0.8	8
111	Growth of GaSb and AlSb quantum dots on high-index GaAs substrates. Applied Physics Express, 2014, 7, 055502.	2.4	8
112	Double-Sided Nonalloyed Ohmic Contacts to Si-doped GaAs for Plasmoelectronic Devices. ACS Omega, 2019, 4, 7300-7307.	3.5	8
113	Magneto photoluminescence in droplet epitaxial GaAs quantum rings. Physica Status Solidi (B): Basic Research, 2009, 246, 861-863.	1.5	7
114	Fine structure splitting reduction in droplet epitaxy GaAs quantum dots grown on (111)A surface. Journal of Physics: Conference Series, 2010, 245, 012049.	0.4	7
115	FABRICATION OF A GaAs/AlGaAs LATTICE-MATCHED QUANTUM DOT SOLAR CELL. Journal of Nonlinear Optical Physics and Materials, 2010, 19, 681-686.	1.8	7
116	Photocurrent characteristics in p-i-n diodes with built-in coupled or uncoupled multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 349-351.	0.8	7
117	Scanning Fabry-PÃ©rot interferometer with largely tuneable free spectral range for high resolution spectroscopy of single quantum dots. Review of Scientific Instruments, 2011, 82, 073103.	1.3	7
118	Growth of GaSb quantum dots on GaAs (311)A. Journal of Crystal Growth, 2013, 378, 475-479.	1.5	7
119	Impacts of ambipolar carrier escape on current-voltage characteristics in a type-I quantum-well solar cell. Applied Physics Letters, 2013, 103, 061118.	3.3	7
120	Design and fabrication of photonic crystal resonators for single-mode and vertical surface emission from strain-compensated quantum cascade lasers operating at 4.32 Î¼m. Applied Physics Express, 2021, 14, 102003.	2.4	7
121	Angle-resolved reflection spectra of Dirac cones in triangular-lattice photonic crystal slabs. Optics Express, 2020, 28, 21601.	3.4	7
122	Automated angle-scanning photoemission end-station with molecular beam epitaxy at KEK-PF BL-1C. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2001, 467-468, 1497-1501.	1.6	6
123	Self-organized template formation for quantum dot ordering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1912-1916.	2.1	6
124	Quantum dot decoherence measured by ensemble photoluminescence. Journal of Applied Physics, 2005, 98, 103527.	2.5	6
125	Fabrication of Al nanoparticles and their electrical properties studied by capacitanceâ€“voltage measurements. Applied Surface Science, 2006, 252, 5408-5410.	6.1	6
126	EFFECTS OF ANTIMONY FLUX ON MORPHOLOGY AND PHOTOLUMINESCENCE SPECTRA OF GaSb QUANTUM DOTS FORMED ON GaAs BY DROPLET EPITAXY. Journal of Nonlinear Optical Physics and Materials, 2010, 19, 819-826.	1.8	6

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127	Self-Assembly of GaAs Quantum Wires Grown on (311)A Substrates by Droplet Epitaxy. Applied Physics Express, 2011, 4, 055501.	2.4	6
128	Size-dependent contact angle of Ga droplets on GaAs. Journal of Crystal Growth, 2013, 378, 5-7.	1.5	6
129	Superlinear Photoluminescence Dynamics in Plasmonâ€"Quantum-Dot Coupling Systems. ACS Photonics, 2018, 5, 897-906.	6.6	6
130	Anisotropic expansion of drifting spin helices in GaAs quantum wells. Physical Review B, 2021, 103, .	3.2	6
131	Eigenmode symmetry assignment of triangular-lattice photonic crystal slabs and their Dirac cones materialized by effective degeneracy in the mid-infrared region. Optics Express, 2021, 29, 19486.	3.4	6
132	Real-time and space visualization of excitations of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î½</mml:mi><mml:mo>=</mml:mo><mml:mn>1</mml:n fractional quantum Hall edge. Physical Review Research, 2022, 4, .	3.6	6
133	Magneto-photoluminescence study of InGaAs quantum dots fabricated by droplet epitaxy. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 448-451.	2.7	5
134	Picosecond Time-Resolved Bleaching Dynamics of Self-Assembled Quantum Dots. IEEE Nanotechnology Magazine, 2004, 3, 348-352.	2.0	5
135	Advanced quantum dot and photonic crystal technologies for integrated nanophotonic circuits. Microelectronics Journal, 2009, 40, 736-740.	2.0	5
136	Spontaneous formation of a cluster of InAs dots along a ring-like zone on GaAs (100) by droplet epitaxy. Journal of Crystal Growth, 2009, 311, 1836-1838.	1.5	5
137	Optical anisotropy of GaSb type-II nanorods on vicinal (111)B GaAs. Applied Physics Letters, 2011, 99, 231901.	3.3	5
138	Fabrication of InAs nanoscale rings by droplet epitaxy. Journal of Crystal Growth, 2013, 378, 529-531.	1.5	5
139	Emission from a dipole-forbidden energy state in a GaAs quantum-ring induced by dressed photon. Applied Physics A: Materials Science and Processing, 2014, 115, 1-4.	2.3	5
140	Spin-locked transport in a two-dimensional electron gas. Physical Review B, 2020, 101, .	3.2	5
141	Polarization Anisotropies in Strain-Free, Asymmetric, and Symmetric Quantum Dots Grown by Droplet Epitaxy. Nanomaterials, 2021, 11, 443.	4.1	5
142	Currentâ€"Voltage Characteristics of GaAs/AlGaAs Coupled Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND08.	1.5	5
143	Patchwork metasurface quantum well photodetectors with broadened photoresponse. Optics Express, 2021, 29, 59.	3.4	5
144	Dichroic reflection of InAsâˆ•GaAs quantum dots. Journal of Applied Physics, 2005, 98, 073519.	2.5	4

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145	Structure of Nanowires Fabricated by Electron Beam Induced Deposition to Connect Self-Assembled Quantum Structures. Japanese Journal of Applied Physics, 2007, 46, 6277-6281.	1.5	4
146	Quantum dots to double concentric quantum ring structures transition. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 928-931.	0.8	4
147	Growth of GaSb and InSb quantum dots on GaAs (311)A by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 275-277.	0.8	4
148	Type-II recombination dynamics of tensile-strained GaP quantum dots in GaAs grown by droplet epitaxy. Applied Physics Letters, 2016, 109, 171902.	3.3	4
149	Hyperfine-controlled domain-wall motion observed in real space and time. Physical Review B, 2016, 94, .	3.2	4
150	Strain Relaxation in GaSb/GaAs(111)A Heteroepitaxy Using Thin InAs Interlayers. ACS Omega, 2018, 3, 15592-15597.	3.5	4
151	Exciton Dynamics in Droplet Epitaxial Quantum Dots Grown on (311)A-Oriented Substrates. Nanomaterials, 2020, 10, 1833.	4.1	4
152	Self-assembled Semiconductor Quantum Ring Complexes by Droplet Epitaxy: Growth and Physical Properties. Nanoscience and Technology, 2014, , 161-196.	1.5	4
153	Effects of Sb/As Interdiffusion on Optical Anisotropy of GaSb Quantum Dots in GaAs Grown by Droplet Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 115201.	1.5	4
154	One-dimensional single (In,Ga)As quantum dot arrays formed by self-organized anisotropic strain engineering. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 568-572.	2.7	3
155	Carrier capture and relaxation through a continuum background in InAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 163-166.	2.7	3
156	Circular dichroism inInAsâˆ•GaAsquantum dots: Confinement-induced magnetism. Physical Review B, 2006, 74, .	3.2	3
157	Two-Color Photoexcitation in a GaNAs/AlGaAs Quantum Well Solar Cell. Japanese Journal of Applied Physics, 2012, 51, 06FF15.	1.5	3
158	Currentâ€"Voltage Characteristics of GaAs/AlGaAs Coupled Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND08.	1.5	3
159	Self-assembly of Ga droplets attached to GaAs quantum dots. Journal of Crystal Growth, 2013, 378, 53-56.	1.5	3
160	Postâ€growth annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1505-1508.	0.8	3
161	GaAs/AlGaAs quantum wells with indirect-gap AlGaAs barriers for solar cell applications. Applied Physics Letters, 2014, 104, .	3.3	3
162	Nonlocal biphoton generation in a Werner state from a single semiconductor quantum dot. Physical Review B, 2015, 91, .	3.2	3

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163	Optical transitions in GaNAs quantum wells with variable nitrogen content embedded in AlGaAs. AIP Advances, 2016, 6, .	1.3	3
164	Bias voltage dependence of two-step photocurrent in GaAs/AlGaAs quantum well solar cells. Journal of Applied Physics, 2016, 119, .	2.5	3
165	Transmission and reflection of charge-density wave packets in a quantum Hall edge controlled by a metal gate. Applied Physics Letters, 2018, 112, .	3.3	3
166	Annealing-Induced Structural Evolution of InAs Quantum Dots on InP (111)A Formed by Droplet Epitaxy. Crystal Growth and Design, 2021, 21, 3947-3953.	3.0	3
167	Anomalous Capacitanceâ€"Voltage Characteristics of GaAs/AlGaAs Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND07.	1.5	3
168	Formation of InGaAs Quantum Disks Using Droplet Lithography. Japanese Journal of Applied Physics, 2007, 46, L736-L738.	1.5	2
169	Magneto-photoluminescence study in single GaAs/AlGaAs self-assembled quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1982-1984.	2.7	2
170	Line broadening of excitonic complexes in selfâ€assembled GaAs/AlGaAs single quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 886-889.	0.8	2
171	Electronic structure of GaAs/AlGaAs quantum double rings in lateral electric field. Chinese Optics Letters, 2009, 7, 882-885.	2.9	2
172	Thermal annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2742-2744.	2.7	2
173	Photo-induced current in n-AlGaAs/GaAs heterojunction channels driven by local illumination at the edge regions of Hall bar. Applied Physics Letters, 2013, 102, 252104.	3.3	2
174	Tight-binding analysis of the electronic states in AlAs with N isoelectronic impurities. Journal of Applied Physics, 2014, 115, 123501.	2.5	2
175	Nonlinear optical response of embedded-semiconductor quantum dots covered by plasmonic metasurfaces. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	2
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